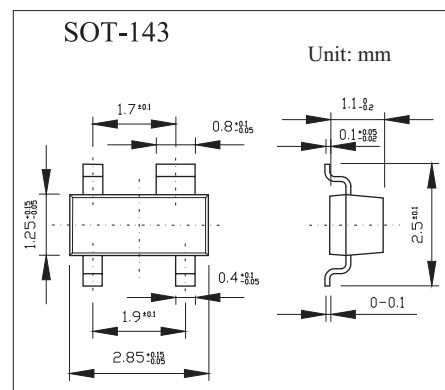


Silicon Switching Diode Array

BAW100

■ Features

- For high-speed switching
- Electrically insulated diodes

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse voltage	V_R	75	V
Peak reverse voltage	V_{RM}	85	V
Forward current	I_F	200	mA
Surge forward current, $t = 1\ \mu\text{s}$	I_{FS}	4.5	A
Total power dissipation, $T_s = 31^\circ\text{C}$	P_{tot}	330	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-65 to +150	$^\circ\text{C}$
Junction - ambient ¹⁾	$R_{th JA}$	≤ 500	K/W
Junction - soldering point	$R_{th JS}$	≤ 360	K/W

Note

1.Package mounted on epoxy pcb $40\text{ mm} \times 40\text{ mm} \times 1.5\text{ mm}/6\text{ cm}^2\text{ Cu}$

BAW100■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	V_{BR}	$I_{(BR)} = 100\ \mu\text{A}$	85			V
Forward voltage	V_F	$I_F = 1\text{ mA}$			715	mV
		$I_F = 10\text{ mA}$			855	
		$I_F = 50\text{ mA}$			1000	
		$I_F = 150\text{ mA}$			1250	
Reverse current	I_R	$V_R = 75\text{ V}$			1	μA
		$V_R = 25\text{ V}, T_A = 150^\circ\text{C}$			30	
		$V_R = 75\text{ V}, T_A = 150^\circ\text{C}$			50	
Diode capacitance	C_d	$V_R = 0\text{ V}, f = 1\text{ MHz}$			2	pF
Reverse recovery time	t_{rr}	$I_F = 10\text{ mA}, I_R = 10\text{ mA}, R_L = 100\ \Omega$ measured at $I_R = 1\text{ mA}$			6	ns

■ Marking

Marking	JSs
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